

ABSTRACT

Provided is a method of producing a GaAs single crystal having high carrier concentration and high crystallinity and to provide a GaAs single crystal wafer using such a GaAs single crystal.

In the method of producing a GaAs single crystal, a vertical boat method is performed with a crucible 4 receiving a seed crystal 10, a Si material 12, a GaAs material 14 serving as an impurity, solid silicon dioxide 16, and a boron oxide material 18, thereby growing a GaAs single crystal 20.

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